MOSPEC

SILICON NPN POWER TRANSISTORS

PNP

MJ2955

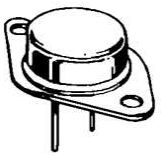
15 AMPERES
COMPLEMENTARY
SILICON
POWER TRANSISTORS
60 VOLTS
115 WATTS

DESCRIPTION :

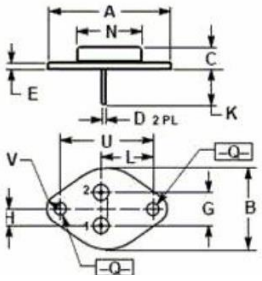
- Excellent Safe Operating Area
- DC Current Gain-hFE=20-70@I_C = -4A
- Collector-Emitter Saturation Voltage-
  : $V_{CE(SAT)}$= -1.1V(Max) @ I_C = -4A
- Complement to Type 2N3055
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

APPLICATIONS :

- Designed for general-purpose switching and amplifiers applications



TO-3



PIN 1.BASE.
2.EMITTER
3.COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	39.00	
B	25.3	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
O	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

Characteristic	Symbol	MJ2955	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current-Continuous	I_C	-15	A
Base Current	I_B	-7	A
Collector Power Dissipation @T_C=25℃	P_C	115	Watts
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{th\ j\text{-}c}$	1.52	°C/W

ELECTRICAL CHARATERISTICS (T_C=25^{O}C unless otherwise noted)

Characteristic	Symbol	Min.	Max	Unit
OFFCHARACTERISTICS				
Collector-Emitter Sustaining Voltage (I_C = -200 mA, I_B = 0)	$V_{CEO(SUS)}$	-60		V
Collector-Emitter Sustaining Voltage (I_C = -200 mA, R_{BE} = 100 Ohms)	V_{CER}	-70		V
Collector Cutoff Current (V_{CE} = -30 V, I_B = 0)	I_{CEO}		-0.7	mA
Collector Cutoff Current (V_{CE} = -100 V, $V_{BE(OFF)}$ = -1.5V) (V_{CE} = -100 V, $V_{BE(OFF)}$ = -1.5V, T_C = 150℃)	I_{CEX}		-1 -5	mA
Emitter Cutoff Current (V_{EB}= -7.0 V, I_C = 0)	I_{EBO}		-5	mA
ON CHARACTERISTICS				
DC Current Gain (I_C = -4 A, V_{CE} = -4 V) (I_C = -10 A, V_{CE} = -4 V)	h_{FE}	20 5	70	
Collector-Emitter Saturation Voltage (I_C = -4 A, I_B = -0.4 A) (I_C = -10 A, I_B = -3.3 A)	$V_{CE(SAT)}$		-1.1 -3.0	V
Base-Emitter On Voltage (I_C = -4 A, V_{CE} = -4 V)	$V_{BE(ON)}$		-1.5	V
DYNAMIC CHARATERISTICS				
Current gain-Bandwidth product (I_C=-0.5 A ,V_{CE} =-10 V, f =1.0 MHz	f_T	2.5		MHz

Notice

MOSPEC reserves the rights to make changes of the content herein the document anytime without notification. MOSPEC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies. Please refer to MOSPEC website for the last document.

MOSPEC disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially incurred.

Application shown on the herein document are examples of standard use and operation. Customers are responsible for comprehending suitable use in particular applications. MOSPEC makes no representation or warranty that such application will be suitable for the specified use without further testing or modification.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by MOSPEC for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of MOSPEC or others.

These MOSPEC products are intended for usage in general electronic equipment. Please make sure to consult with MOSPEC before you use these MOSPEC products in equipment which require specialized quality and/or reliability, and in equipment which could have major impact to the welfare of human life (atomic energy control, aeronautics , traffic control, combustion control, safety devices etc.)